

General purpose transistor (isolated transistor and diode)

QSL11

A 2SB1710 and a RB461F are housed independently in a TSMT5 package.

● Applications

DC / DC converter
Motor driver

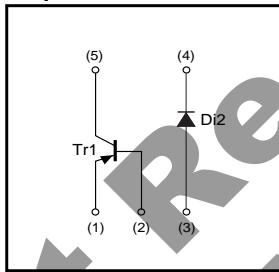
● Features

- 1) Tr : Low $V_{CE}(\text{sat})$
 - 2) Small package

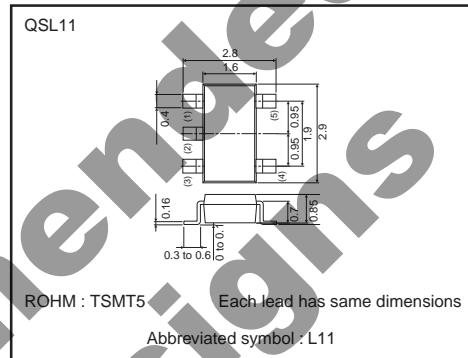
● Structure

Silicon epitaxial planar transistor Schottky barrier diode

● Equivalent circuit



●External dimensions (Unit : mm)



●Packaging specifications

Type	QSL11
Package	TSMT5
Marking	L11
Code	TR
Basic ordering unit(pieces)	3000

Transistors

●Absolute maximum ratings ($T_a=25^\circ C$)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-1	A
	I_{CP}	-2	A ^{*1}
Power dissipation	P_C	0.9	W/ ELEMENT ^{*2}
Junction temperature	T_j	150	°C
Range of storage temperature	T_{STG}	-40 to +125	°C

^{*1} Single pulse, $P_w=1\text{ms}$ ^{*2} Mounted on a 25mm×25mm×0.8mm ceramic substrate

Di2

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	25	V
Reverse voltage (DC)	V_R	20	V
Average rectified forward current	I_F	700	mA
Forward current surge peak (60Hz, 1∞)	I_{FSM}	3	A
Power dissipation	P_D	0.7	W/ ELEMENT *
Junction temperature	T_j	125	°C
Range of storage temperature	T_{STG}	-40 to +125	°C

* Mounted on a 25mm×25mm×0.8mm ceramic substrate

Tr1&Di2

Parameter	Symbol	Limits	Unit
Total power dissipation	P_D	0.5	W/ TOTAL ^{*1}
		1.25	W/ TOTAL ^{*2}

^{*1} Each terminal mounted on a recommended land^{*2} Mounted on a 25mm×25mm×0.8mm ceramic substrate●Electrical characteristics ($T_a=25^\circ C$)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	-30	-	-	V	$I_C=-10\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	-30	-	-	V	$I_C=-1mA$
Emitter-base breakdown voltage	BV_{EBO}	-6	-	-	V	$I_E=-10\mu A$
Collector cutoff current	I_{CBO}	-	-	-100	nA	$V_{CB}=-30V$
Emitter cutoff current	I_{EBO}	-	-	-100	nA	$V_{EB}=-6V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-150	-350	mV	$I_C=-500mA, I_E=-25mA$
DC current gain	h_{FE}	270	-	680	-	$V_{CE}=-2V, I_C=-100mA$ *
Transition frequency	f_T	-	320	-	MHz	$V_{CE}=-2V, I_E=100mA, f=100MHz$ *
Collector output capacitance	C_{OB}	-	7	-	pF	$V_{CB}=-10V, I_E=0A, f=1MHz$

* Pulsed

Di2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	-	450	490	mV	$I_F=700mA$
Reverse current	I_R	-	-	200	μA	$V_R=20V$
Reverse recovery time	t_{rr}	-	9	-	ns	$I_F=I_R=100mA, I_{rr}=0.1I_R$

Transistors

● Electrical characteristic curves

Tr1

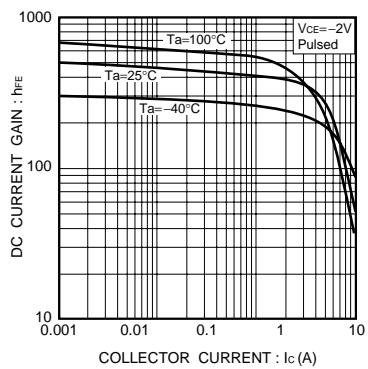


Fig.1 DC current gain vs. collector current

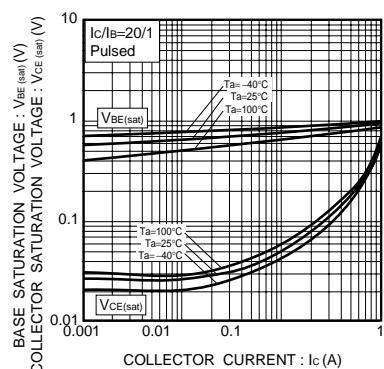


Fig.2 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

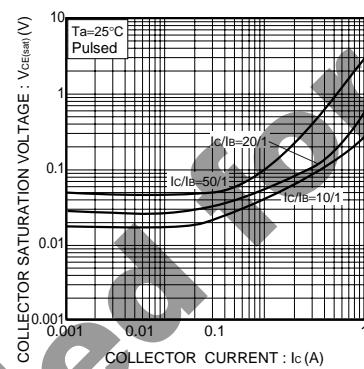


Fig.3 Collector-emitter saturation voltage vs. collector current

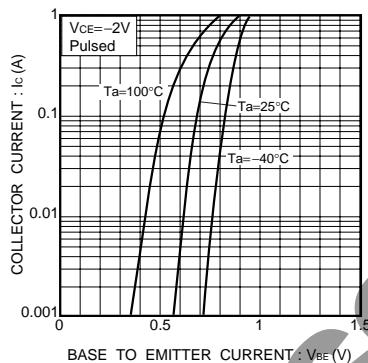


Fig.4 Grounded emitter propagation characteristics

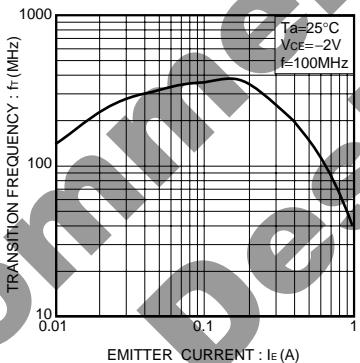


Fig.5 Gain bandwidth product vs. emitter current

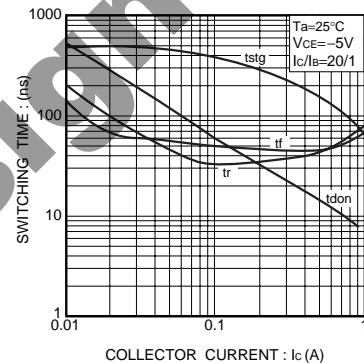
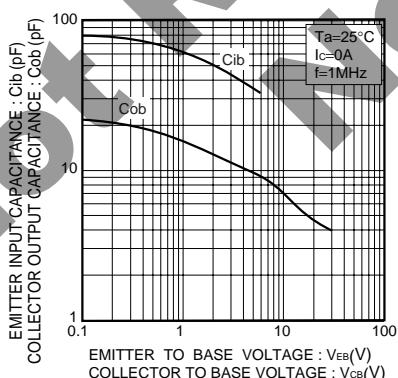


Fig.6 Switching time

Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

Transistors

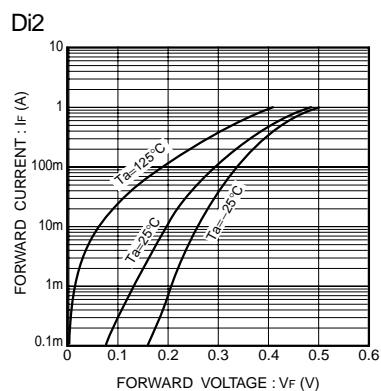


Fig.9 Forward characteristics

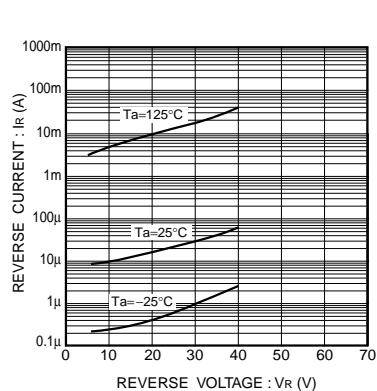


Fig.10 Reverse characteristics

Not Recommended for
New Designs

Appendix

Notes

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